

Abstract

The thin film transistor substrate increases an aperture ratio as well as prevents shorts between pixel electrodes by connecting drain electrodes of thin film transistors to storage electrodes to reduce the number of holes contacting the pixel electrodes. In the method of forming the thin film transistor substrate, drain electrode patterns are formed such that drain electrodes included in thin film transistors are electrically connected to storage electrodes included in storage capacitors. Accordingly, the number of holes contacting the pixel electrodes can be reduced so that an aperture ratio can be increased, or shorts between pixel electrodes can be prevented. Also, the drain electrode patterns are formed from the same conductive layer as the data lines supplying data signals to the thin film transistors, and a constant spacing between the two can be obtained to maintain a uniform parasitic capacitance therebetween and prevent deterioration of the data signal.